

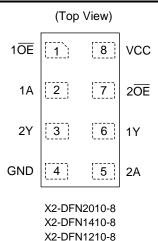


DUAL BUFFER GATE WITH 3-STATE OUTPUTS

Description

The 74LVC2G125 is a dual buffer gate with 3-state outputs. The device is designed for operation over a power supply range of 1.65V to 5.5V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down.

Pin Assignments



Features

- Wide Supply Voltage Range from 1.65 to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption
- I_{OFF} Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall times. The hysteresis is typically 100mV at V_{CC} = 3.0V.
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

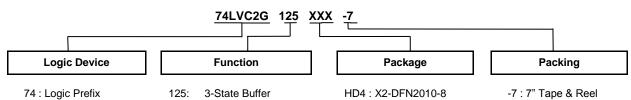
- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide Array of Products Such as:
 - PCs, Networking, Notebooks, Netbooks, PDAs
 - Tablet Computers, E-readers
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set Top Boxes
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information (Note 4)



LVC: 1.65V to 5.5V Logic Family 2G: Dual Gate

3-State Buffer OE - Low

HD4: X2-DFN2010-8 HK3: X2-DFN1410-8 RA3: X2-DFN1210-8

-7: 7" Tape & Reel

	Package	Package	Package	7" Tape and Re	el (Note 6)
Device	Code	(Note 5)	Size	Quantity	Part Number Suffix
74LVC2G125HD4-7	HD4	X2-DFN2010-8	1.95mm x 1.0mm x 0.4mm 0.5 mm lead pitch	5,000/Tape & Reel	-7
74LVC2G125HK3-7	HK3	X2-DFN1410-8	1.35mm x 1.0mm x 0.35mm 0.4 mm lead pitch	5,000/Tape & Reel	-7
74LVC2G125RA3-7	RA3	X2-DFN1210-8	1.2mm x 1.0mm x 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

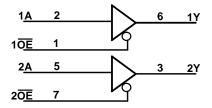
Notes: 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

- 5. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html.
- 6. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Description		
1 OE	1	Output Enable for buffer 1		
1A	2	Data Input		
2Y	3	Data Output		
GND	4	Ground		
2A	5	Data Input		
1Y	6	Data Output		
2 OE	7	Output Enable for buffer 2		
Vcc	8	Supply Voltage		

Logic Diagram



Function Table

Inp	Output	
ŌĒ	Α	Y
L	Н	Н
L	L	L
Н	X	Z



Absolute Maximum Ratings (Notes 7 & 8)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
Vcc	Supply Voltage	-0.5 to +6.5	V
VI	Input Voltage	-0.5 to +6.5	V
Vo	Output Voltage -Active Mode	-0.5 to V _{CC} +0.5	V
Vo	Output Voltage Power Down Mode	-0.5 to +6.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
I _{OK}	Output Clamp Current (Vo < 0 OR Vo > Vcc)	±50	mA
lo	Continuous Output Current (Vo = 0 to Vcc)	±50	mA
Icc	Continuous Current Through V _{CC}	100	mA
I _{GND}	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 9)

Symbol	Pa	Min	Max	Unit		
.,	On and the self-the sec	Operating	1.65	5.5	.,	
V _{CC}	Operating Voltage	Data Retention Only	1.5	_	V	
VI	Input Voltage		0	5.5	V	
\/-	Output Voltage Active Mode		0	Vcc	V	
Vo	Output Voltage Power-Down Mode		0	5.5	V	
	I _{OH} High-Level Output Current	V _{CC} = 1.65V	_	-4		
		V _{CC} = 2.3V	_	-8	mA	
		V _{CC} = 2.7V	_	-12		
IOH		V 2.0V	_	-16		
		$V_{CC} = 3.0V$		-24		
		$V_{CC} = 4.5V$	_	-32		
		V _{CC} = 1.65V	_	4		
		V _{CC} = 2.3V	_	8		
I.e.	Low-Level Output Current	V _{CC} = 2.7V	_	12	mA	
loL	Low-Level Output Current	V 0.0V	_	16	mA	
		$V_{CC} = 3.0V$	_	24		
		V _{CC} = 4.5V	_	32		
A+/A>/	land Transition Disc or Fall Date	V _{CC} = 1.65V to 2.7V	_	20		
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 2.7V to 5.5V	_	10	ns/V	
T _A	Operating Fr	ee-Air Temperature	-40	+125	°C	

Note: 9. Unused inputs should be held at V_{CC} or Ground.

^{7.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{8.} Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics (All typical values are at $T_A = +25$ °C)

		T 10 111	.,	-40	°C to +8	5°C	-40°C to	+125°C	
Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур.	Max	Min	Max	Unit
			V _{CC} = 1.65V to 1.95V	0.65 x V _{CC}	_	_	0.65 x V _{CC}	_	
	V _{IH} High-Level Input Voltage		V _{CC} = 2.3V to 2.7V	1.7	_	_	1.7	_	
V_{IH}		-	_	V _{CC} = 2.7V to 3.6V	2.0	_	_	2.0	_
			V _{CC} = 4.5V to 5.5V	0.7 x V _{CC}	_	_	0.7 x V _{CC}	_	
			V _{CC} = 1.65V to 1.95V	_	_	0.35 x V _{CC}	_	0.35 x V _{CC}	
.,	Low-Level		V _{CC} = 2.3V to 2.7V	_	_	0.7	_	0.7	l
V_{IL}	Input Voltage	_	V _{CC} = 2.7V to 3.6V	_	_	0.8	_	0.8	V
			$V_{CC} = 4.5 \text{V to } 5.5 \text{V}$	_	_	0.3 x V _{CC}	_	0.3 x V _{CC}	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} - 0.1	Vcc	_	V _{CC} - 0.1	_	
		I _{OH} = -4mA	1.65V	1.2	1.53	_	0.95	_	
	High-Level	I _{OH} = -8mA	2.3V	1.9	2.13	_	1.7	_	
V_{OH}	Output	I _{OH} = -12mA	2.7	2.2	2.5	_	1.9	_	V
	Voltage	I _{OH} = -16mA	2) /	2.4	2.7	_	2.2	_	
		I _{OH} = -24mA	3V	2.3	2.6	_	2.0	_	
		I _{OH} = -32mA	4.5V	3.8	4.1	_	3.4	_	
	l l	I _{OL} = 100μA	1.65V to 5.5V	_	0	0.1	_	0.1	
		I _{OL} = 4mA	1.65V	_	0.08	0.45	_	0.7	
	Low-Level	$I_{OL} = 8mA$	2.3V	_	0.14	0.3	_	0.45	
V_{OL}	Output Voltage	$I_{OL} = 12mA$	2.7V	_	0.19	0.4	_	0.6	V
		I _{OL} = 16mA	0) /	_	0.25	0.4	_	0.6	
		$I_{OL} = 24mA$	3V	_	0.37	0.55	_	0.8	
		$I_{OL} = 32mA$	4.5V	_	0.43	0.55	_	0.8	
II	Input Current	V _I = 5.5V or GND	0V to 5.5V	_	± 0.1	±5	_	± 20	μΑ
l _{OZ}	Z-State Leakage Current	$V_I = V_{IH}$ or V_{IL} $V_O = 5.5V$ or GND	3.6V	_	± 0.1	± 10	_	±20	μА
l _{OFF}	Power Down Leakage Current	$V_1 \text{ or } V_0 = 5.5V$	0V	_	± 0.1	±10	_	±20	μА
Icc	Supply Current	$V_1 = 5.5V$ or GND $I_0=0A$	1.65V to 5.5V	_	0.1	10	_	40	μΑ
ΔI _{CC}	Additional Supply Current	One input at V _{CC} –0.6V Other inputs at V _{CC} or GND	2.3V to 5.5V	_	5	500	_	5,000	μА
Cı	Input Capacitance	V _I = V _{CC} or GND	3.3V	_	2.5	_	_	_	pF



Operating Characteristics

	Parameter	Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{cc} = 5V Typ.	Unit
	Power Dissipation	f = 10MHz output enabled	17	17	17	17	pF
C_{pd}	Capacitance	f = 10MHz output disabled	5	5	5	5	pF

Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур.	Max	Unit	
	Thermal Resistance Junction-		X2-DFN2010-8		_	313	_	
θ_{JA}		X2-DFN1410-8	(Note 10)	_	321	_	°C/W	
	to-Ambient	X2-DFN1210-8		_	395	_		
	- 15	X2-DFN2010-8		_	145	_		
θ _{JC} Thei to-C	Thermal Resistance Junction-	X2-DFN1410-8	(Note 10)	_	166	_	°C/W	
	to-case	X2-DFN1210-8		_	236	_		

Note: 10. Test condition for each package type: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

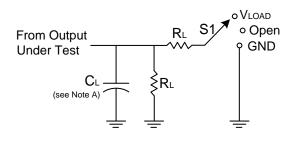
Switching Characteristics

Typical Values at $T_A = +25$ °C and nominal voltages 1.8V, 2.5V, 2.7V, 3.3V, and 5.0V. See Figure 1.

Donomoton	From	То	V	T _A =	= -40°C to +8	35°C	T _A = -40°C	to +125°C	l l m it							
Parameter	Input Output		V _{CC}	Min	Тур	Max	Min	Max	Unit							
			1.8V ± 0.15V	1.0	3.7	9.1	1.0	11.4								
			2.5V ± 0.2V	0.5	2.5	4.8	0.5	6.0								
t _{pd}	Α	Y	2.7V	1.0	2.7	4.8	1.0	6.0	ns							
			$3.3V \pm 0.3V$	0.5	2.3	4.4	0.5	5.5								
			5.0V ± 0.5V	0.5	1.9	3.7	0.5	4.6								
			1.8V ± 0.15V	1.5	4.3	9.9	1.5	12.4								
			2.5V ± 0.2V	1.0	2.8	5.6	1.0	7.0								
t _{en}	ŌE Y	ŌE	ŌE	OE	ŌE	ŌE	ŌE	ŌE	DE Y	2.7V	1.5	3.3	5.7	1.5	7.1	ns
			$3.3V \pm 0.3V$	0.5	2.4	5.0	0.5	5.9								
			$5.0V \pm 0.5V$	0.5	2.0	3.8	0.5	4.8								
			1.8V ± 0.15V	1.0	3.5	11.6	1.0	14.1								
	dis \overline{OE}			2.5V ± 0.2V	0.5	1.8	5.8	0.5	7.6							
t _{dis}		Y	2.7V	1.0	2.7	4.8	1.0	6.2	ns							
			$3.3V \pm 0.3V$	1.0	2.7	4.6	1.0	5.9								
			5.0V ± 0.5V	0.5	1.8	3.4	0.5	4.6								

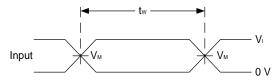


Parameter Measurement Information

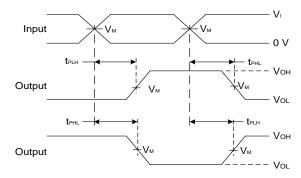


TEST	S1
tplH/tpHL	Open
t _{PLZ} /t _{PZL}	V_{LOAD}
t _{PHZ} /t _{PZH}	GND

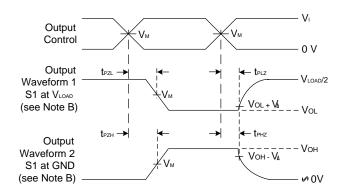
V	Inputs		, ,		Inputs		CL		
V _{CC}	VI	t _r /t _f	VM	V _M V _{LOAD}		RL	V Δ		
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	2 x V _{CC}	30pF	1kΩ	0.15V		
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	2 x V _{CC}	30pF	500Ω	0.15V		
2.7V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V		
3.3V±0.3V	3V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V		
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	2 x V _{CC}	50pF	500Ω	0.3V		



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times

Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

C. Inputs are measured separately one transition per measurement.

D. t_{PLZ} and t_{PHZ} are the same as t_{dis.}

E. t_{PZL} and t_{PZH} are the same as t_{en.}

F. t_{PLH} and t_{PHL} are the same as $t_{pd.}$



Marking Information

(Top View)

<u>Y W X</u>

<u>XX</u>

XX: Identification Code

Y: Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents 52 and 53 week

X: Internal Code

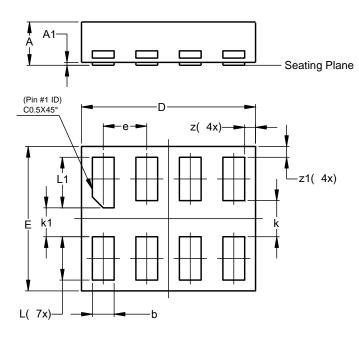
Part Number	Package	Identification Code
74LVC2G125HD4-7	X2-DFN2010-8	9U
74LVC2G125HK3-7	X2-DFN1410-8	9V
74LVC2G125RA3-7	X2-DFN1210-8	9W



X2-DFN1210-8 Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1210-8

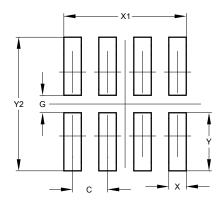


X2-DFN1210-8			
Dim	Min	Max	Тур
Α	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
Е	0.95	1.05	1.00
е	-	-	0.30
k	-	-	0.25
k1	-	-	0.20
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	0.050	0.100	0.075
z 1	0.050	0.100	0.075
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1210-8



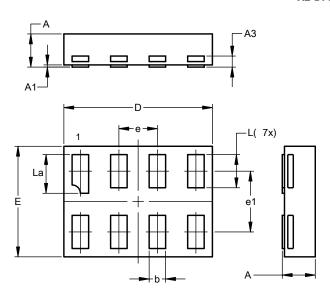
Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Y	0.500	
Y1	1.150	



X2-DFN1410-8 Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1410-8

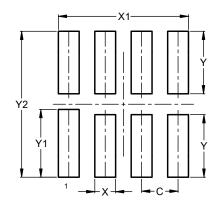


X2-DFN1410-8			
Dim	Min	Max	Тур
Α	0.30	0.35	0.33
A1	0.00	0.03	0.02
A3			0.10
b	0.12	0.20	0.15
D	1.30	1.40	1.35
Е	0.95	1.05	1.00
е			0.35
e1			0.55
L	0.27	0.35	0.30
L1	0.32	0.40	0.35
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1410-8



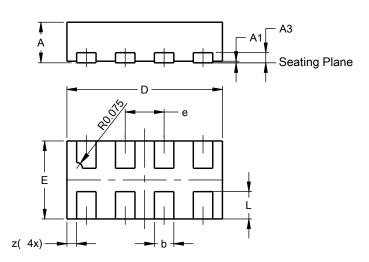
Dimensions	Value	
HILIEUSIOUS	(in mm)	
С	0.350	
Х	0.200	
X1	1.250	
Y	0.600	
Y1	0.650	
Y2	1.400	



X2-DFN2010-8 Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN2010-8

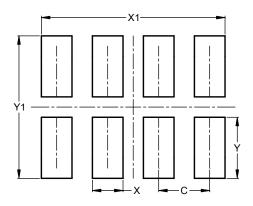


X2-DFN2010-8			
Dim	Min	Max	Тур
Α		0.40	
A1	0.00	0.05	0.02
A3	-		0.13
b	0.20	0.30	0.25
D	1.950	2.05	2.00
Е	0.95	1.05	1.00
е			0.50
L	0.30	0.40	0.35
Z			0.125
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN2010-8



Dimensions	Value	
מווטומווט	(in mm)	
C	0.500	
Х	0.300	
X1	1.800	
Y	0.600	
Y1	1.400	



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